

Customer No.: 31561
Application No.: 10/707,358
Docket No.: 11417-US-PA

AMENDMENTS

In The Claims

Claims 1-19 (canceled).

20.(original) A semiconductor device structure, the structure comprising:

a gate dielectric layer, disposed on a substrate;

a plurality of first gate structures, disposed on the gate dielectric layer, wherein the first gate structures comprise a gate conductive layer, a cap layer and a spacer;

a plurality of second gate structures, disposed on the substrate, wherein the second gate structures comprise the gate conductive layer;

a dielectric layer, disposed on the substrate, covering the first and the second gate structures;

a self-aligned contact, disposed in the dielectric layer between the first gate structures; and

a conductive line, disposed on the dielectric layer, wherein the conductive line electrically connects with the self-aligned contact.

21. (original) The structure of claim 20, wherein the cap layer and the spacer of the first gate structures are disposed between the self-aligned contact and the gate conductive layer.

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22. (withdrawn) The structure of claim 20, wherein the dielectric layer at a sidewall of the gate conductive layer of the second gate structures comprises voids therein.

23. (withdrawn) The structure of claim 22, wherein the dielectric layer at a sidewall of the gate conductive layer of the first gate structures that is not adjacent to the self-aligned contact comprises voids therein.

24. (withdrawn) The structure of claim 20, wherein the second gate structures further comprise a spacer, disposed on a sidewall of the second gate structures, wherein the spacer is higher than the gate conductive layer.

25. (original) The structure of claim 20, wherein a dielectric constant of the dielectric layer is lower than a dielectric constant of the cap layer and the spacer.

26. (original) The structure of claim 20 further comprising a metal silicide layer formed on a sidewall of the gate conductive layer of the second gate structures.

27. (withdrawn) The structure of claim 26, wherein a sidewall of the gate conductive layer of the first gate structures that is not adjacent to the self-aligned

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contact further comprises the metal silicide layer.

Claims 28-31 (canceled).